

Jae-Seong Park

List of Publications by Year in descending order

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31
papers

537
citations

840585

11
h-index

642610

23
g-index

31
all docs

31
docs citations

31
times ranked

689
citing authors

#	ARTICLE	IF	CITATIONS
1	Integration of III-V lasers on Si for Si photonics. <i>Progress in Quantum Electronics</i> , 2019, 66, 1-18.	3.5	86
2	Review of Group III-Nitride-Based Ultraviolet Light-Emitting Diodes: Ways of Increasing External Quantum Efficiency. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, Q42-Q52.	0.9	81
3	Continuous-wave quantum dot photonic crystal lasers grown on on-axis Si (001). <i>Nature Communications</i> , 2020, 11, 977.	5.8	61
4	Heteroepitaxial Growth of III-V Semiconductors on Silicon. <i>Crystals</i> , 2020, 10, 1163.	1.0	56
5	Origin of Defect Tolerance in InAs/GaAs Quantum Dot Lasers Grown on Silicon. <i>Journal of Lightwave Technology</i> , 2020, 38, 240-248.	2.7	46
6	III-V quantum-dot lasers monolithically grown on silicon. <i>Semiconductor Science and Technology</i> , 2018, 33, 123002.	1.0	35
7	Inversion Boundary Annihilation in GaAs Monolithically Grown on On-Axis Silicon (001). <i>Advanced Optical Materials</i> , 2020, 8, 2000970.	3.6	22
8	Recent Progress of Quantum Dot Lasers Monolithically Integrated on Si Platform. <i>Frontiers in Physics</i> , 2022, 10, .	1.0	14
9	Near ultraviolet InGaN/AlGaN-based light-emitting diodes with highly reflective tin-doped indium oxide/Al-based reflectors. <i>Optics Express</i> , 2013, 21, 26774.	1.7	13
10	Highly thermally stable Pd/Zn/Ag ohmic contact to Ga-face p-type GaN. <i>Journal of Alloys and Compounds</i> , 2014, 588, 327-331.	2.8	13
11	Hybrid indium tin oxide/Ag nanowire electrodes for improving the light output power of near ultraviolet AlGaN-based light-emitting diode. <i>Current Applied Physics</i> , 2016, 16, 545-548.	1.1	13
12	Ag nanowire-based electrodes for improving the output power of ultraviolet AlGaN-based light-emitting diodes. <i>Journal of Alloys and Compounds</i> , 2017, 703, 198-203.	2.8	13
13	Use of a patterned current blocking layer to enhance the light output power of InGaN-based light-emitting diodes. <i>Optics Express</i> , 2017, 25, 17556.	1.7	11
14	Formation of an indium tin oxide nanodot/Ag nanowire electrode as a current spreader for near ultraviolet AlGaN-based light-emitting diodes. <i>Nanotechnology</i> , 2017, 28, 045205.	1.3	9
15	Improved Thermal Stability of Ag Ohmic Contacts for GaN-Based Vertical Light-Emitting Diodes Using a Zn Capping Layer. <i>Electrochemical and Solid-State Letters</i> , 2012, 15, H130.	2.2	8
16	Improving the output power of GaN-based light-emitting diode using Ag particles embedded within a SiO ₂ current blocking layer. <i>Superlattices and Microstructures</i> , 2015, 83, 361-366.	1.4	8
17	Formation of low resistance Ti/Al-based ohmic contacts on (111̄) semipolar n-type GaN. <i>Journal of Alloys and Compounds</i> , 2015, 652, 167-171.	2.8	8
18	Using agglomerated Ag grid to improve the light output of near ultraviolet AlGaN-based light-emitting diode. <i>Microelectronic Engineering</i> , 2017, 169, 29-33.	1.1	7

#	ARTICLE	IF	CITATIONS
19	Dependence of thickness and temperature on the thermal stability of Ag films deposited on GaN layers for vertical-geometry GaN-based light-emitting diodes. Superlattices and Microstructures, 2013, 61, 160-167.	1.4	4
20	Improving the output power of near-ultraviolet InGaN/GaN-based light emitting diodes by enhancing the thermal and electrical properties of Ag-based reflector. Superlattices and Microstructures, 2013, 64, 7-14.	1.4	4
21	Single-Mode Photonic Crystal Nanobeam Lasers Monolithically Grown on Si for Dense Integration. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-6.	1.9	4
22	Enhanced thermal stability of Ag ohmic reflector for InGaN/GaN light-emitting diode using a Ru capping layer. Superlattices and Microstructures, 2012, 52, 357-363.	1.4	3
23	Polarity dependence of the electrical characteristics of Ag reflectors for high-power GaN-based light emitting diodes. Applied Physics Letters, 2014, 104, 172104.	1.5	3
24	Graphene diffusion barrier for forming ohmic contact on N-polar n-type GaN for high-power vertical-geometry light-emitting diodes. Applied Physics Express, 2014, 7, 046501.	1.1	3
25	Monolithic III-V quantum dot lasers on silicon. Frontiers of Nanoscience, 2021, 20, 353-388.	0.3	3
26	Silver-induced activation for improving the electrical characteristics of GaN-based vertical light-emitting diodes. Current Applied Physics, 2013, 13, 377-380.	1.1	2
27	Controlling interface oxygen for forming Ag ohmic contact to semi-polar (110 ²) plane p-type GaN. Superlattices and Microstructures, 2014, 75, 962-967.	1.4	2
28	Thermally stable AuBe-based ohmic contacts to p-type GaP for AlGaInP-based light-emitting diode by using a tungsten barrier layer. Journal of the Korean Physical Society, 2016, 68, 306-310.	0.3	2
29	A tantalum diffusion barrier layer for improving the output performance of AlGaInP-based light-emitting diodes. Japanese Journal of Applied Physics, 2016, 55, 032102.	0.8	2
30	Highly reliable Ti-based ohmic contact to N-polar n-type GaN for vertical-geometry light-emitting diodes by using a Ta barrier layer. Optics Express, 2014, 22, A759.	1.7	1
31	A Thermally Stable NiZn/Ta/Ni Scheme to Replace AuBe/Au Contacts in High-Efficiency AlGaInP-Based Light-Emitting Diodes. Journal of Electronic Materials, 2017, 46, 4750-4754.	1.0	0